

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 17 (Cancelled)

Claim 18 (Currently Amended): A method for feeding a gas into a film-forming apparatus having an inner part and an outer part to form a film on a wafer mounted in said inner part in a semiconductor process, comprising steps of:

(a) feeding said gas into a space between said outer part and said inner part and directing a flow of said gas in the direction toward a vertical wall of said outer part to prevent particles adhered to said inner part from peeling off; and

(b) leading said gas into said inner part along a path between said outer part and said inner part so that said gas warms before reaching said inner part.

Claim 19 (Original): The method according to claim 18 wherein said semiconductor process is one of a chemical vapor deposition process and a physical vapor deposition process.

Claim 20 (Original): The method according to claim 19 wherein said film is a silicon nitride film and said particles are Si_xN_4 compounds.

Claim 21 (Original): The method according to claim 20 wherein said process includes steps of:

(c) controlling the temperature in said inner part of said film-forming apparatus in the range of 600°C to 850°C ; and

(d) controlling the pressure in said inner part of said film-forming apparatus in the range of 0.1 torr to 1 torr.

Claim 22 (Original): The method according to claim 20 wherein said gas is a purge gas selected from a group consisting of nitrogen, argon, and other inert gases.

Claim 23 (Original): The method according to claim 22 wherein after said film is formed, said process further includes a step of (e) controlling the flow rate of said gas in the range of 300 sccm to 2000 sccm for 5 min to 15 min to devacuum said film-forming apparatus.